

# Octal 3-State Noninverting D Flip-Flop High-Performance Silicon-Gate CMOS

The MC54/74HC574A is identical in pinout to the LS574. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

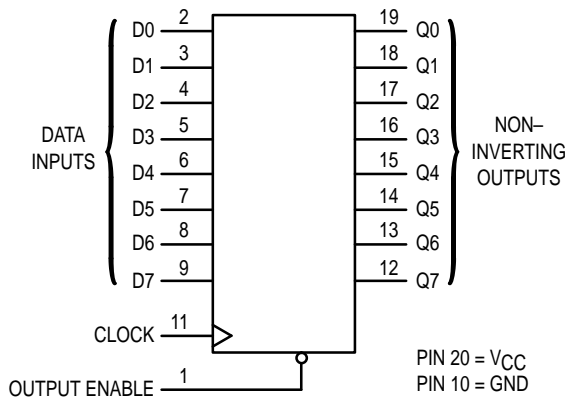
Data meeting the setup time is clocked to the outputs with the rising edge of the Clock. The Output Enable input does not affect the states of the flip-flops, but when Output Enable is high, all device outputs are forced to the high-impedance state. Thus, data may be stored even when the outputs are not enabled.

The HC574A is identical in function to the HCT374A but has the flip-flop inputs on the opposite side of the package from the outputs to facilitate PC board layout.

The HC574A is the noninverting version of the HC564.

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0  $\mu$ A
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 266 FETs or 66.5 Equivalent Gates

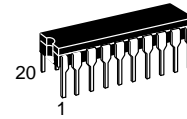
### LOGIC DIAGRAM



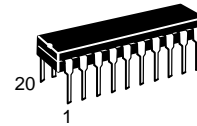
Design Criteria	Value	Units
Internal Gate Count*	66.5	ea
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	$\mu$ W
Speed Power Product	0.0075	pJ

\* Equivalent to a two-input NAND gate.

## MC54/74HC574A



**J SUFFIX**  
CERAMIC PACKAGE  
CASE 732-03



**N SUFFIX**  
PLASTIC PACKAGE  
CASE 738-03

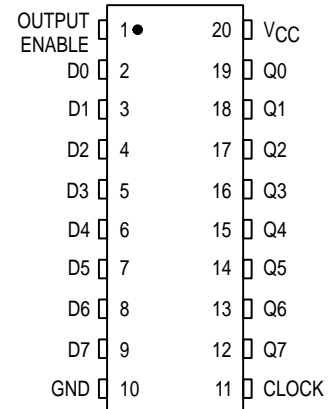


**DW SUFFIX**  
SOIC PACKAGE  
CASE 751D-04

### ORDERING INFORMATION

MC54HCXXXAJ	Ceramic
MC74HCXXXAN	Plastic
MC74HCXXXADW	SOIC

### PIN ASSIGNMENT



### FUNCTION TABLE

Inputs			Output
OE	Clock	D	Q
L		H	H
L		L	L
L	L,H,	X	No Change
H	X	X	Z

X = Don't Care  
Z = High Impedance



# MC54/74HC574A

## MAXIMUM RATINGS\*

Symbol	Parameter	Value	Unit
$V_{CC}$	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
$V_{in}$	DC Input Voltage (Referenced to GND)	- 1.5 to $V_{CC} + 1.5$	V
$V_{out}$	DC Output Voltage (Referenced to GND)	- 0.5 to $V_{CC} + 0.5$	V
$I_{in}$	DC Input Current, per Pin	$\pm 20$	mA
$I_{out}$	DC Output Current, per Pin	$\pm 35$	mA
$I_{CC}$	DC Supply Current, $V_{CC}$ and GND Pins	$\pm 75$	mA
$P_D$	Power Dissipation in Still Air, Plastic or Ceramic DIP† SOIC Package†	750 500	mW
$T_{stg}$	Storage Temperature	- 65 to + 150	°C
$T_L$	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package) (Ceramic DIP)	260 300	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range  $GND \leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$ . Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

\* Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

† Derating — Plastic DIP: -10 mW/°C from 65° to 125°C  
Ceramic DIP: -10 mW/°C from 100° to 125°C  
SOIC Package: -7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
$V_{CC}$	DC Supply Voltage (Referenced to GND)	2.0	6.0	V	
$V_{in}, V_{out}$	DC Input Voltage, Output Voltage (Referenced to GND)	0	$V_{CC}$	V	
$T_A$	Operating Temperature, All Package Types	- 55	+ 125	°C	
$t_r, t_f$	Input Rise and Fall Time (Figure 1)	$V_{CC} = 2.0 \text{ V}$ $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 0 0	1000 500 400	ns

## DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	$V_{CC}$ V	Guaranteed Limit			Unit
				- 55 to 25°C	$\leq 85^\circ\text{C}$	$\leq 125^\circ\text{C}$	
$V_{IH}$	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \leq 20 \mu\text{A}$	2.0	1.5	1.5	1.5	V
			4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
$V_{IL}$	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \leq 20 \mu\text{A}$	2.0	0.5	0.5	0.5	V
			4.5	1.35	1.35	1.35	
			6.0	1.8	1.8	1.8	
$V_{OH}$	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \leq 20 \mu\text{A}$	2.0	1.9	1.9	1.9	V
			4.5	4.4	4.4	4.4	
		4.5	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \leq 6.0 \text{ mA}$ $ I_{out}  \leq 7.8 \text{ mA}$	3.98	3.84	3.7	
				6.0	5.48	5.34	
$V_{OL}$	Maximum Low-Level Output Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \leq 20 \mu\text{A}$	2.0	0.1	0.1	0.1	V
			4.5	0.1	0.1	0.1	
			6.0	0.1	0.1	0.1	
		4.5	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \leq 6.0 \text{ mA}$ $ I_{out}  \leq 7.8 \text{ mA}$	0.26	0.33	0.4	
6.0	0.26			0.33	0.4		
$I_{in}$	Maximum Input Leakage Current	$V_{in} = V_{CC} \text{ or } GND$	6.0	$\pm 0.1$	$\pm 1.0$	$\pm 1.0$	$\mu\text{A}$

NOTE: Information on typical parametric values can be found in Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

**DC ELECTRICAL CHARACTERISTICS** (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	Guaranteed Limit			Unit
				- 55 to 25°C	≤ 85°C	≤ 125°C	
I <sub>OZ</sub>	Maximum Three-State Leakage Current	Output in High-Impedance State V <sub>in</sub> = V <sub>IL</sub> or V <sub>IH</sub> V <sub>out</sub> = V <sub>CC</sub> or GND	6.0	± 0.5	± 5.0	± 10	μA
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	V <sub>in</sub> = V <sub>CC</sub> or GND  I <sub>out</sub>   = 0 μA	6.0	4.0	40	160	μA

**AC ELECTRICAL CHARACTERISTICS** (C<sub>L</sub> = 50 pF, Input t<sub>r</sub> = t<sub>f</sub> = 6.0 ns)

Symbol	Parameter	V <sub>CC</sub> V	Guaranteed Limit			Unit
			- 55 to 25°C	≤ 85°C	≤ 125°C	
f <sub>max</sub>	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 4)	2.0 4.5 6.0	6.0 30 35	4.8 24 28	4.0 20 24	MHz
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Clock to Q (Figures 1 and 4)	2.0 4.5 6.0	160 32 27	200 40 34	240 48 41	ns
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Maximum Propagation Delay, Output Enable to Q (Figures 2 and 5)	2.0 4.5 6.0	150 30 26	190 38 33	225 45 38	ns
t <sub>PZL</sub> , t <sub>PZH</sub>	Maximum Propagation Delay, Output Enable to Q (Figures 2 and 5)	2.0 4.5 6.0	140 28 24	175 35 30	210 42 36	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, any Output (Figures 1 and 4)	2.0 4.5 6.0	60 12 10	75 15 13	90 18 15	ns
C <sub>in</sub>	Maximum Input Capacitance		10	10	10	pF
C <sub>out</sub>	Maximum Three-State Output Capacitance, Output in High-Impedance State		15	15	15	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

C <sub>PD</sub>	Power Dissipation Capacitance (Per Enabled Output)*	Typical @ 25°C, V <sub>CC</sub> = 5.0 V			pF
		24			
		24			

\* Used to determine the no-load dynamic power consumption: P<sub>D</sub> = C<sub>PD</sub> V<sub>CC</sub><sup>2</sup>f + I<sub>CC</sub> V<sub>CC</sub>. For load considerations, see Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

**TIMING REQUIREMENTS** (C<sub>L</sub> = 50 pF, Input t<sub>r</sub> = t<sub>f</sub> = 6.0 ns)

Symbol	Parameter	Fig.	V <sub>CC</sub> Volts	Guaranteed Limit						Unit	
				- 55 to 25°C		≤ 85°C		≤ 125°C			
				Min	Max	Min	Max	Min	Max		
t <sub>su</sub>	Minimum Setup Time, Data to Clock	3	2.0 4.6 6.0	50 10 9.0		65 13 11		75 15 13		ns	
t <sub>h</sub>	Minimum Hold Time, Clock to Data	3	2.0 4.5 6.0	5.0 5.0 5.0		5.0 5.0 5.0		5.0 5.0 5.0		ns	
t <sub>w</sub>	Minimum Pulse Width, Clock	1	2.0 4.5 6.0	75 15 13		95 19 16		110 22 19		ns	
t <sub>r</sub> , t <sub>f</sub>	Maximum Input Rise and Fall Times	1	2.0 4.5 6.0		1000 500 400		1000 500 400		1000 500 400		ns

SWITCHING WAVEFORMS

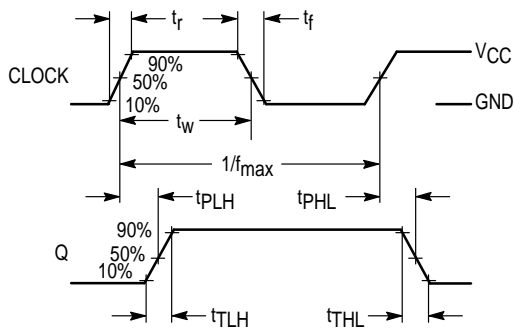


Figure 1.

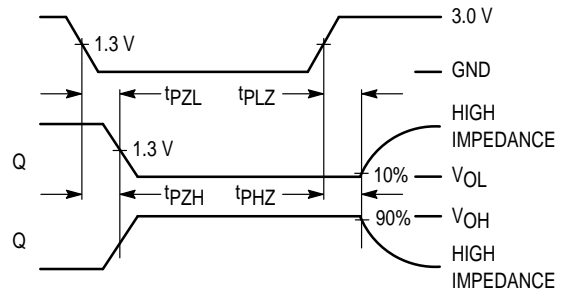


Figure 2.

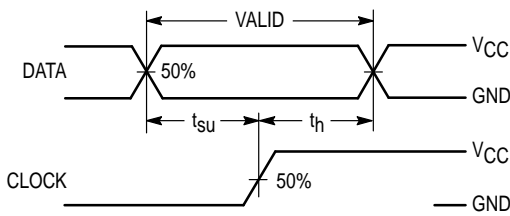
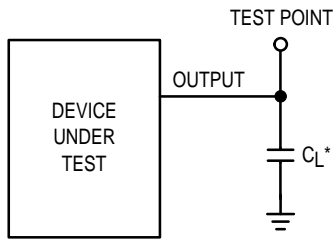
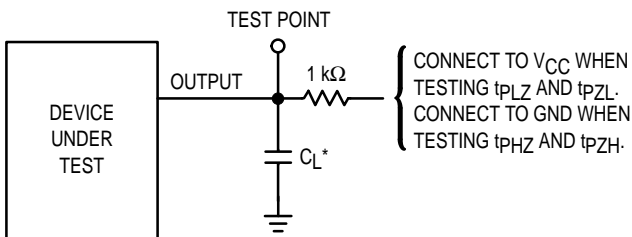


Figure 3.



\* Includes all probe and jig capacitance

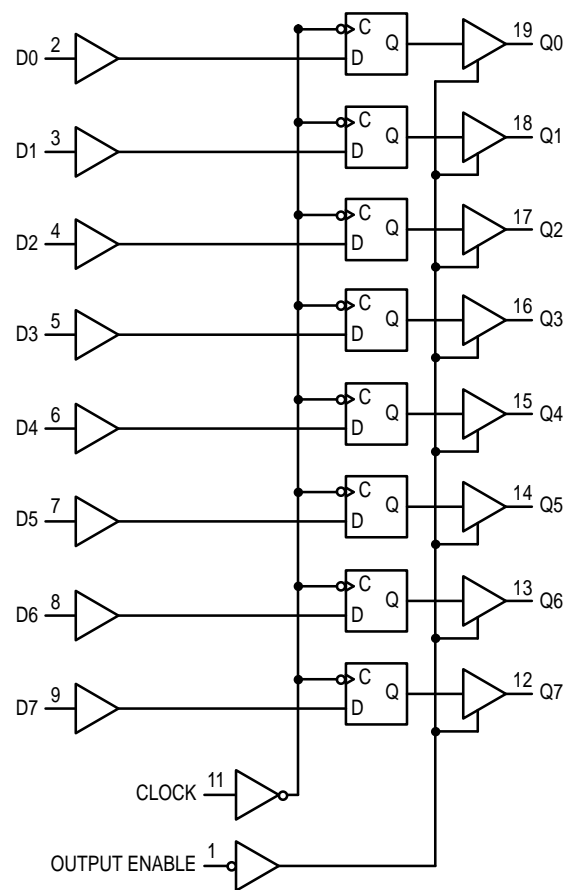
Figure 4.



\* Includes all probe and jig capacitance

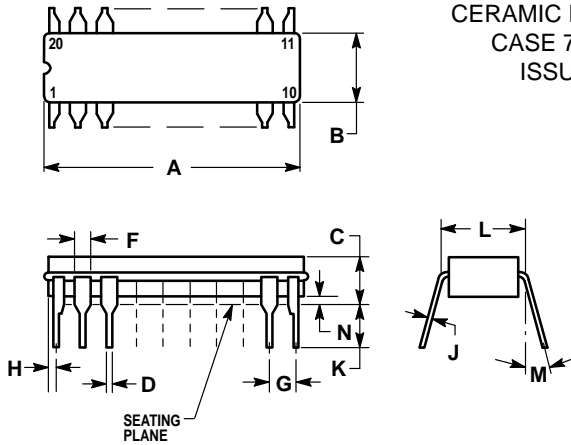
Figure 5. Test Circuit

EXPANDED LOGIC DIAGRAM



OUTLINE DIMENSIONS

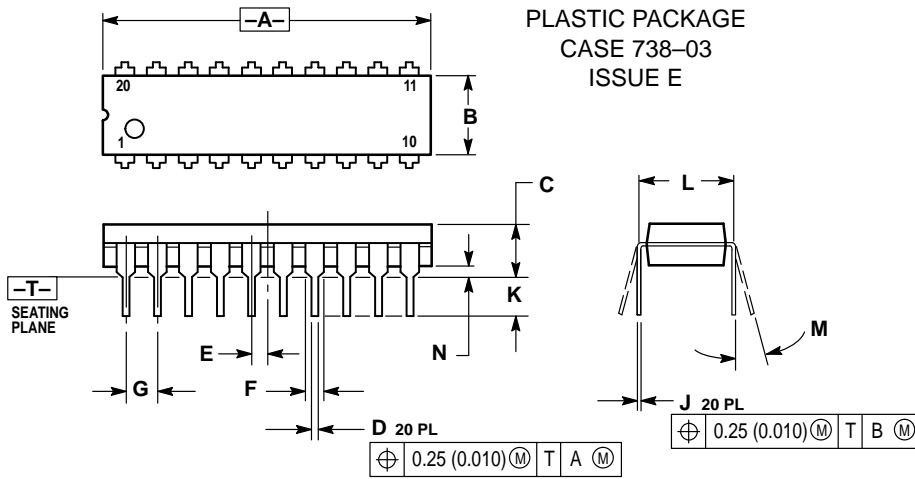
**J SUFFIX**  
**CERAMIC PACKAGE**  
 CASE 732-03  
 ISSUE E



- NOTES:
- LEADS WITHIN 0.25 (0.010) DIAMETER, TRUE POSITION AT SEATING PLANE, AT MAXIMUM MATERIAL CONDITION.
  - DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
  - DIMENSIONS A AND B INCLUDE MENISCUS.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	23.88	25.15	0.940	0.990
B	6.60	7.49	0.260	0.295
C	3.81	5.08	0.150	0.200
D	0.38	0.56	0.015	0.022
F	1.40	1.65	0.055	0.065
G	2.54 BSC		0.100 BSC	
H	0.51	1.27	0.020	0.050
J	0.20	0.30	0.008	0.012
K	3.18	4.06	0.125	0.160
L	7.62 BSC		0.300 BSC	
M	0° 15°		0° 15°	
N	0.25	1.02	0.010	0.040

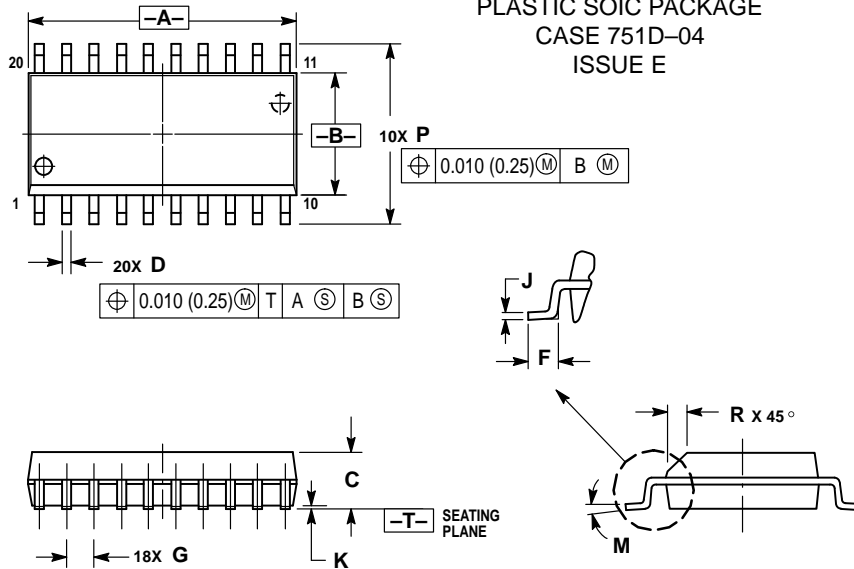
**N SUFFIX**  
**PLASTIC PACKAGE**  
 CASE 738-03  
 ISSUE E



- NOTES:
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  - CONTROLLING DIMENSION: INCH.
  - DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
  - DIMENSION B DOES NOT INCLUDE MOLD FLASH.


DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.010	1.070	25.66	27.17
B	0.240	0.260	6.10	6.60
C	0.150	0.180	3.81	4.57
D	0.015	0.022	0.39	0.55
E	0.050 BSC		1.27 BSC	
F	0.050	0.070	1.27	1.77
G	0.100 BSC		2.54 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.140	2.80	3.55
L	0.300 BSC		7.62 BSC	
M	0° 15°		0° 15°	
N	0.020	0.040	0.51	1.01

**DW SUFFIX**  
**PLASTIC SOIC PACKAGE**  
 CASE 751D-04  
 ISSUE E



- NOTES:
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  - CONTROLLING DIMENSION: MILLIMETER.
  - DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
  - MAXIMUM MOLD PROTRUSION 0.150 (0.006) PER SIDE.
  - DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.13 (0.005) TOTAL IN EXCESS OF D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	12.65	12.95	0.499	0.510
B	7.40	7.60	0.292	0.299
C	2.35	2.65	0.093	0.104
D	0.35	0.49	0.014	0.019
F	0.50	0.90	0.020	0.035
G	1.27 BSC		0.050 BSC	
J	0.25	0.32	0.010	0.012
K	0.10	0.25	0.004	0.009
M	0° 7°		0° 7°	
P	10.05	10.55	0.395	0.415
R	0.25	0.75	0.010	0.029

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